

Set	Items	Description
S1	55351	(DIGITAL OR ELECTRONIC?) (3N) (DISPLAY? OR SCREEN?)
S2	718463	FLAT? ? OR FLATTEN? ? OR FLATTENING? ?
S3	1116733	SHEET? ?
S4	740655	WARP????? OR CRACK?
S5	787503	VACUUM?
S6	51772	CHUCK? ?
S7	372555	LIGHT(2N)EMIT?
S8	2295075	DISPLAY? OR SCREEN?
S9	15341	S2(3N)S3
S10	720	S9 AND S8
S11	17	S10 AND S4
S12	1	S6 AND S11
S13	50546	(S2 OR FLATTENED) AND S3
S14	4633	S5 AND S6
S15	19	S13 AND S14
S16	19	RD (unique items)
S17	18	S16 NOT S11
S18	43795	S3 AND ELECTROD?
S19	7	S18 AND (ROW? ? OR COLUMN? ?) AND S7
S20	7	RD (unique items)
S21	6	S20 NOT (S11 OR S15)
S22	1446	(S2 OR FLATTENED) AND S3 AND S4
S23	6	S22 AND S6
S24	4	S23 NOT (S11 OR S15 OR S21)
S25	2	S1 AND S22
S26	2	RD (unique items)
S27	1	S26 NOT (S11 OR S15 OR S21 OR S24)

? show files

File 2:INSPEC 1969-2003/Jul W1  
(c) 2003 Institution of Electrical Engineers

File 6:NTIS 1964-2003/Jul W2  
(c) 2003 NTIS, Intl Cpyrght All Rights Res

File 8:Bi Compendex(R) 1970-2003/Jul W1  
(c) 2003 Elsevier Eng. Info. Inc.

File 34:SciSearch(R) Cited Ref Sci 1990-2003/Jul W1  
(c) 2003 Inst for Sci Info

File 434:SciSearch(R) Cited Ref Sci 1974-1989/Dec  
(c) 1998 Inst for Sci Info

File 35:Dissertation Abs Online 1861-2003/Jun  
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File 65:Inside Conferences 1993-2003/Jul W2  
(c) 2003 BLDSC all rts. reserv.

File 144:Pascal 1973-2003/Jul W1  
(c) 2003 INIST/CNRS

File 99:Wilson Appl. Sci & Tech Abs 1983-2003/Jun  
(c) 2003 The HW Wilson Co.

File 94:JICST-EPlus 1985-2003/Jun W5  
(c)2003 Japan Science and Tech Corp(JST)

File 347:JAPIO Oct 1976-2003/Mar(Updated 030703)  
(c) 2003 JPO & JAPIO

File 350:Derwent WPIX 1963-2003/UD,UM &UP=200345  
(c) 2003 Thomson Derwent

11/9/12 (Item 6 from file: 350)  
DIALOG(R) File 350:Derwent WPIX  
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011702974 \*\*Image available\*\*  
WPI Acc No: 1998-119884/199811  
XRAM Acc No: C98-039311  
XRPX Acc No: N98-095436

Annealing glass sheets especially for flat panel displays - while supported vertically in frame holding multiple sheets to minimise warping

Patent Assignee: CORNING INC (CORG )

Inventor: HOUSE K L

Number of Countries: 002 Number of Patents: 002

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
US 5711778	A	19980127	US 9616780	A	19960507	199811 B
			US 96670963	A	19960626	
JP 10053427	A	19980224	JP 97116813	A	19970507	199818

Priority Applications (No Type Date): US 9616780 P 19960507; US 96670963 A 19960626

Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 5711778	A	6		C03B-025/00	Provisional application US 9616780
JP 10053427	A	5		C03B-025/02	

Abstract (Basic): US 5711778 A

Multiple glass sheets are annealed while assembled vertically in a frame which separates them while engaging parts of all four edges of each sheet. Preferably the frame comprises edge members each having slots for receiving the edges of the sheets. A clamp may apply a force to each of two edge members in the plane of the sheets and in the direction of the other two members.

USE - Treatment of sheets for flat panel display units where high degree of annealing is required.

ADVANTAGE - Vertical orientation of sheets minimises warping while edge support eliminates surface damage. Slotted edge members of frame permit expansion and contraction of sheets during annealing further reducing warping .

Dwg.1/5

Title Terms: ANNEAL; GLASS; SHEET; FLAT; PANEL; DISPLAY ; SUPPORT;

VERTICAL; FRAME; HOLD; MULTIPLE; SHEET; MINIMISE; WARP

Derwent Class: L01; L03; U11; U14

International Patent Class (Main): C03B-025/00; C03B-025/02

File Segment: CPI; EPI

Manual Codes (CPI/A-N): L01-G02; L03-G05

Manual Codes (EPI/S-X): U11-C03J2A; U11-C03J8; U14-K01A5

11/9/13 (Item 7 from file: 350)  
DIALOG(R) File 350:Derwent WPIX  
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010691394 \*\*Image available\*\*  
WPI Acc No: 1996-188350/199619  
Related WPI Acc No: 1997-128536; 1997-179005; 1997-358325  
XRAM Acc No: C96-060154

Mfg. flat glass sheets by forming crack in larger glass sheet using laser - involves covering the sheet with protective polymer layer to

**protect surface from chips arising during breaking**

Patent Assignee: CORNING INC (CORG )

Inventor: STEVENS H J

Number of Countries: 020 Number of Patents: 008

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
WO 9609254	A1	19960328	WO 95US9728	A	19950726	199619 B
US 5622540	A	19970422	US 94308276	A	19940919	199722
EP 782548	A1	19970709	EP 95929350	A	19950726	199732
			WO 95US9728	A	19950726	
JP 10506087	W	19980616	WO 95US9728	A	19950726	199834
			JP 96510869	A	19950726	
KR 97706212	A	19971103	WO 95US9728	A	19950726	199844
			KR 97701758	A	19970318	
TW 336218	A	19980711	TW 95109088	A	19950829	199847
EP 782548	B1	20011212	EP 95929350	A	19950726	200204
			WO 95US9728	A	19950726	
DE 69524613	E	20020124	DE 624613	A	19950726	200215
			EP 95929350	A	19950726	
			WO 95US9728	A	19950726	

Priority Applications (No Type Date): US 94308276 A 19940919

Cited Patents: DE 4320341; US 4544395; US 5084604; US 5254833; WO 9320015

Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
WO 9609254	A1	E	17	C03B-021/00	
				Designated States (National): JP KR	
				Designated States (Regional): AT BE CH DE DK ES FR GB GR IE IT LU MC NL PT SE	
US 5622540	A		6	G03B-021/02	
EP 782548	A1	E		C03B-021/00	Based on patent WO 9609254
				Designated States (Regional): DE FR GB NL	
JP 10506087	W		16	C03B-033/09	Based on patent WO 9609254
KR 97706212	A			C03B-021/00	Based on patent WO 9609254
TW 336218	A			C03B-033/02	
EP 782548	B1	E		C03B-021/00	Based on patent WO 9609254
				Designated States (Regional): DE FR GB NL	
DE 69524613	E			C03B-021/00	Based on patent EP 782548
					Based on patent WO 9609254

Abstract (Basic): WO 9609254 A

**Flat glass sheets** are mfd. by covering at least one of the two major surfaces of a larger **flat glass sheet** (10) with a protective layer (12) of organic material, removing a portion of the protective layer to form a covered region and a non-covered region and a non-covered region (14), and forming a **crack** along a desired line of separation in the non-covered region.

USE - Method is used to produce glass sheets of any size from larger glass sheets, initially continuous sheet, by breaking them but protecting them during breaking.

ADVANTAGE - Method yields sheets with higher dimensional and surface quality suitable for critical applications such as liquid crystal **display** panels, and glass surface being protected from chips created during breaking operations as well as any dirt or dust in the atmos..

Dwg.1/3

Abstract (Equivalent): US 5622540 A

A method for manufacturing **flat glass sheets** comprises: providing a **flat glass sheet** having two major surfaces; covering at least one of the major surfaces with a protective layer of organic material; and sweeping a laser over the glass sheet in a

single pass to selectively remove a portion of the protective layer, thereby forming, on at least one major surface, a covered region and a non-covered region; and

form a **crack** in the glass sheet along a desired line of separation in the non-covered region.

Dwg.1/3

Title Terms: MANUFACTURE; FLAT; GLASS; SHEET; FORMING; **CRACK** ; LARGER; GLASS; SHEET; LASER; COVER; SHEET; PROTECT; POLYMER; LAYER; PROTECT; SURFACE; CHIP; ARISE; BREAK

Derwent Class: L01; P82

International Patent Class (Main): C03B-021/00; C03B-033/02; C03B-033/09; G03B-021/02

International Patent Class (Additional): B23K-026/00; C03B-023/26

File Segment: CPI; EngPI

Manual Codes (CPI/A-N): L01-D; L01-G07

?

17/9/4 (Item 3 from file: 347)  
DIALOG(R) File 347:JAPIO  
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06798857 \*\*Image available\*\*  
VACUUM CHUCK AND COATING FORMING DEVICE

PUB. NO.: 2001-026340 [JP 2001026340 A]  
PUBLISHED: January 30, 2001 (20010130)  
INVENTOR(s): TRAN DEAN  
DAVID M CUBBERLEY  
DAVID H BOGER  
GEORGE J VENTURA JR  
ALAN M HIRSCHBERG  
APPLICANT(s): TRW INC  
APPL. NO.: 2000-142631 [JP 2000142631]  
FILED: May 16, 2000 (20000516)  
PRIORITY: 316991 [US 99316991], US (United States of America), May 24,  
1999 (19990524)  
INTL CLASS: B65H-005/22; B05C-013/02; B65G-049/06; B65H-029/24;  
C23C-016/458; H01L-031/04

#### ABSTRACT

PROBLEM TO BE SOLVED: To provide a vacuum chuck to hold thin sheet materials and a device to form a uniform coating substantially on the thin sheet material using the vacuum chuck.

SOLUTION: A vacuum chuck is provided with a chuck main body 36, a valve member 56 and a holding shim 58. The chuck main body 36 is provided with a gas permeable supporting surface 38 supporting a thin sheet material so that it marks off a vacuum chamber with an entrance 54. The valve member 56 controls gas flow through the vacuum chamber entrance. The holding shim 58 holds the valve member in the vacuum chamber entrance. The holding shim 58 enables the valve member to be pulled back partially from the vacuum chamber entrance in order to support the thin sheet material flat substantially on the gas permeable supporting surface and to allow the absorption of vacuum in the vacuum chamber. The holding shim can respond to the vacuum chamber entrance when connected to a vacuum source, and seal the vacuum chamber to maintain the vacuum in it. The valve member is inserted into the vacuum chamber entrance fully in order to hold the thin sheet material on the gas permeable supporting surface. Accordingly, the holding shim can respond to the vacuum chamber entrance when it is removed from the vacuum source. The device is provided with a conveyor to transfer the vacuum chuck on it.

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17/9/5 (Item 4 from file: 347)  
DIALOG(R) File 347:JAPIO  
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05916847 \*\*Image available\*\*  
METHOD AND APPARATUS FOR MEASURING WARP OF THIN SHEET

PUB. NO.: 10-199947 [JP 10199947 A]  
PUBLISHED: July 31, 1998 (19980731)  
INVENTOR(s): FUJITA TADASHIGE  
MIURA AKIRA

YAGIHARA TAKESHI  
KOBAYASHI SHINJI  
OKA SADAJI

APPLICANT(s): TERA TEC KK [000000] (A Japanese Company or Corporation), JP  
(Japan)  
APPL. NO.: 09-003978 [JP 973978]  
FILED: January 13, 1997 (19970113)  
INTL CLASS: [6] H01L-021/66; G01B-011/24; G03F-007/207; H01L-021/027  
JAPIO CLASS: 42.2 (ELECTRONICS -- Solid State Components); 29.1 (PRECISION  
INSTRUMENTS -- Photography & Cinematography); 46.1  
(INSTRUMENTATION -- Measurement); 46.2 (INSTRUMENTATION --  
Testing)

#### ABSTRACT

PROBLEM TO BE SOLVED: To measure the warp of a thin **sheet**, such as semiconductor wafers by obtaining the warp value of the **sheet** from data of the focus position measured by automatic focusing, without making a means for holding the wafer **flat** act on the **sheet** under measurement, utilizing a stepper aligner.

SOLUTION: On a wafer stage 2 a wafer 1 under measurement is laid, and measuring points are set to set an exposing region at a usual exposure, utilizing a function for moving the stage 2 in directions x and y. A **vacuum chuck** is stopped from acting on the wafer 1, the stage 2 is moved in a z-direction to detect an optimum focus, and the warp value at each point is obtained from the position data in the z-direction, the data of the focus obtained for every small region of the wafer 1. The measurement is repeated to obtain data, which are collected and processed by a data processor 7, to obtain the warp of the entire wafer 1 and its stress distribution.

17/9/11 (Item 10 from file: 347)  
DIALOG(R) File 347:JAPIO  
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03034035 \*\*Image available\*\*  
METHOD AND DEVICE OF MANUFACTURING THIN BASE **SHEET**

PUB. NO.: 02-009535 [JP 2009535 A]  
PUBLISHED: January 12, 1990 (19900112)  
INVENTOR(s): KIMURA TAKESAKU  
APPLICANT(s): CITIZEN WATCH CO LTD [000196] (A Japanese Company or  
Corporation), JP (Japan)  
APPL. NO.: 63-159331 [JP 88159331]  
FILED: June 29, 1988 (19880629)  
INTL CLASS: [5] B23P-013/00; H01L-021/304; H01L-021/304  
JAPIO CLASS: 25.2 (MACHINE TOOLS -- Cutting & Grinding); 42.2 (ELECTRONICS  
-- Solid State Components)  
JAPIO KEYWORD: R005 (PIEZOELECTRIC FERROELECTRIC SUBSTANCES)  
JOURNAL: Section: M, Section No. 951, Vol. 14, No. 144, Pg. 57, March  
19, 1990 (19900319)

#### ABSTRACT

PURPOSE: To simplify a manufacturing process by a method wherein, in a manufacture of a thin base **sheet**, e.g. crystal, silicon, the end surface of an ingot is ground in a **flat** manner and the end surface side is cut to a thin piece with a given thickness, and the thin piece is mounted to a **chuck** to grind a cut surface.

CONSTITUTION: The end surface of an ingot 22 supported by a support means 20 is ground through rotation of a grinding stone 43 by moving slide 3 and a moving table 7, and is then cut to a thin piece 25 by means of a blade 13 of a thin base sheet cutting means 10. A thin base sheet 25 is adsorbed by a vacuum chuck 56, and in turn is adsorbed by a vacuum chuck 59 of a rotary disc 57 to release the thin base plate from attraction of the chuck 56, and the thin base sheet 25 is turned over by rotating the rotary disc 57 in a 180 deg. arc. Thereafter, the thin base sheet is adsorbed by a vacuum chuck 35 of a support member 33 to render attraction of the chuck 59 ineffective, and the cut surface of the thin base sheet 25 is ground through rotation of a grinding stone 43. The above motion is repeated through orderly movement of the slide 3 and the moving table 7, the thin base sheet 25 is formed, in order, and is contained in a cassette 60 for carry-out. This constitution simplifies a manufacturing process and enables improvement of quality.

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24/9/1 (Item 1 from file: 347)  
DIALOG(R)File 347:JAPIO  
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05169502 \*\*Image available\*\*  
ELECTROSTATIC CHUCK AND ITS MANUFACTURE

PUB. NO.: 08-125002 [JP 8125002 A]  
PUBLISHED: May 17, 1996 (19960517)  
INVENTOR(s): KAWAMINAMI SHUICHI  
APPLICANT(s): NIPPON CEMENT CO LTD [000419] (A Japanese Company or Corporation), JP (Japan)  
APPL. NO.: 06-283918 [JP 94283918]  
FILED: October 25, 1994 (19941025)  
INTL CLASS: [6] H01L-021/68; B23Q-003/15  
JAPIO CLASS: 42.2 (ELECTRONICS -- Solid State Components); 25.2 (MACHINE TOOLS -- Cutting & Grinding)  
JAPIO KEYWORD:R004 (PLASMA)

#### ABSTRACT

PURPOSE: To uniformize the thickness of a dielectric body and to improve the suction of an electrostatic chuck by baking a substrate formed of Al(sub 2)O(sub 3) or AlN ceramics, by flattening the surface by polishing, and by overlaying it with an electrode which contains Pd and Ag in a specific quantity or less and a dielectric body which consists mainly of TiO(sub 2).

CONSTITUTION: An electrostatic chuck has a dielectric body on the top layer, an electrode on the middle layer and a substrate on the bottom layer, and TiO(sub 2) is used for the dielectric body to improve dielectric constant and improve suction. For the electrode, Pd-Ag material which can be baked in the atmosphere is used, and the material is composed of Ag of 65wt.% or less, concerning the baking temperature. The substrate is formed of Al(sub 2)O(sub 3) or AlN ceramics. The substrate is prebaked, its surface is flattened by polishing and overlaid with the electrode. A dielectric sheet is bonded by thermocompression to form the electrostatic chuck. Thus, even when the dielectric sheet, which is bonded by thermocompression, is baked on the top plane of the flattened substrate, almost no substrate warpage is allowed on the substrate, so that the thickness of the dielectric body on the top plane is uniformized.

24/9/2 (Item 2 from file: 347)  
DIALOG(R)File 347:JAPIO  
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02078818 \*\*Image available\*\*  
SHEET FLATTENING CHUCK

PUB. NO.: 61-292918 [JP 61292918 A]  
PUBLISHED: December 23, 1986 (19861223)  
INVENTOR(s): TANIGUCHI MOTOYA  
FUNATSU RYUICHI  
KUJI TOMOHIRO  
KENBO YUKIO  
INAGAKI AKIRA  
APPLICANT(s): HITACHI LTD [000510] (A Japanese Company or Corporation), JP (Japan)  
APPL. NO.: 60-134084 [JP 85134084]  
FILED: June 21, 1985 (19850621)



INTL CLASS: [4] H01L-021/30; B23Q-003/00; H01L-021/68  
JAPIO CLASS: 42.2 (ELECTRONICS -- Solid State Components); 25.2 (MACHINE  
TOOLS -- Cutting & Grinding)  
JAPIO KEYWORD: R005 (PIEZOELECTRIC FERROELECTRIC SUBSTANCES)  
JOURNAL: Section: E, Section No. 508, Vol. 11, No. 154, Pg. 164, May  
19, 1987 (19870519)

ABSTRACT

PURPOSE: To improve the reliability of miniaturization, thinning and connections, by omitting electric wirings to several vertically movable elements in a wafer flattening chuck flattening the surface of a wafer having warpage and undulations.

CONSTITUTION: Contact probes 10 with two electrodes are each connected to the lower sections of a plurality of piezo elements 3 deforming a chuck plate 2, to which a wafer 1 is fixed, in the vertical direction from the back of the chuck plate 2, and a printed substrate 11 to which a predetermined wiring pattern is formed is brought into contact with the contact probes 10, thus supplying several piezo element 3 with voltage. Accordingly, electric wirings to respective element 3 are unnecessary, thus improving the reliability of connections, then miniaturizing, lightening and thinning the whole chuck.

24/9/3 (Item 1 from file: 350)  
DIALOG(R) File 350:Derwent WPIX  
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012541239 \*\*Image available\*\*  
WPI Acc No: 1999-347345/199929  
XRPX Acc No: N99-259715

Electrostatic chuck for processing semiconducting wafers  
Patent Assignee: SHERMAN A (SHER-I)  
Inventor: SHERMAN A  
Number of Countries: 082 Number of Patents: 003  
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
WO 9925063	A1	19990520	WO 98US23444	A	19981104	199929 B
AU 9913042	A	19990531	AU 9913042	A	19981104	199941
US 6141203	A	20001031	US 94205923	A	19940303	200057
			US 96617948	A	19960315	
			US 97965867	A	19971107	

Priority Applications (No Type Date): US 97965867 A 19971107; US 94205923 A 19940303; US 96617948 A 19960315

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

WO 9925063 A1 E 35 H02N-013/00

Designated States (National): AL AM AT AU AZ BA BB BG BR BY CA CH CN CU CZ DE DK EE ES FI GB GE GH GM HR HU ID IL IS JP KE KG KP KR KZ LC LK LR LS LT LU LV MD MG MK MN MW MX NO NZ PL PT RO RU SD SE SG SI SK SL TJ TM TR TT UA UG UZ VN YU ZW

Designated States (Regional): AT BE CH CY DE DK EA ES FI FR GB GH GM GR IE IT KE LS LU MC MW NL OA PT SD SE SZ UG ZW

AU 9913042	A	H02N-013/00	Based on patent WO 9925063
US 6141203	A	H02N-013/00	CIP of application US 94205923
			CIP of application US 96617948
			CIP of patent US 5535090
			CIP of patent US 5867359

Abstract (Basic): WO 9925063 A1

NOVELTY - The electrostatic chuck (8) has two small electrostatic

structures (A,B) for holding an electrically conductive workpiece (10). Each structure includes a first thermally conductive single crystal dielectric **sheet** (22) and a first electrode in **sheet** form (23) sandwiched between the first (22) and second dielectric **sheet** (24)

USE - Semiconductor fabrication in low pressure environment

ADVANTAGE - Can be used to process wafers at any temperature, can **flatten warped wafers**

DESCRIPTION OF DRAWING(S) - Cross section of electrostatic **chuck**  
pp; 35 DwgNo 1/12

Title Terms: ELECTROSTATIC; **CHUCK** ; PROCESS; SEMICONDUCTOR; WAFER

Derwent Class: U11; V06

International Patent Class (Main): H02N-013/00

File Segment: EPI

Manual Codes (EPI/S-X): U11-F02A2; V06-M06F; V06-U

24/9/4 (Item 2 from file: 350)

DIALOG(R)File 350:Derwent WPIX

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010419415 \*\*Image available\*\*

WPI Acc No: 1995-320730/199541

Related WPI Acc No: 1999-142233

XRPX Acc No: N95-241249

**Electrostatic chuck for holding conductive work piece such as semiconductor wafer - has several small electrostatic structures forming one plate of capacitor and workpiece forming other plate**

Patent Assignee: SHERMAN A (SHER-I)

Inventor: SHERMAN A

Number of Countries: 018 Number of Patents: 002

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
WO 9524070	A1	19950908	WO 95US2636	A	19950302	199541 B
US 5535090	A	19960709	US 94205923	A	19940303	199633

Priority Applications (No Type Date): US 94205923 A 19940303

Cited Patents: US 4502094; US 5055964; US 5103367; US 5179498; US 5384681

Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
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WO 9524070	A1	E	24	H02N-013/00	
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Designated States (National): JP

Designated States (Regional): AT BE CH DE DK ES FR GB GR IE IT LU MC NL PT SE

US 5535090	A		12	H02N-013/00	
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Abstract (Basic): WO 9524070 A

The electrostatic **chuck** includes a thermally conductive base plate which attaches the **chuck** to a low pressure reactor. Several electrostatic structures over the base form a capacitor plate. Each structure includes two thermally conductive dielectric **sheets**, an electrode, and a device which applies potentials to the electrode. The electrode is in surface contact with one of the **sheets**.

A workpiece forms a second capacitor plate and is held by the first dielectric **sheet** of each of the structures under application of the different potentials. The base plate is metal with a smooth sealing surface. The dielectric **sheet** is formed of segments of sapphire.

USE/ADVANTAGE - For mounting semiconductor wafers. Secure at high temperatures due to materials used. Improved **flattening of warped wafers**. Avoids damage to wafer due to voltage breakdown. reliable.

Dwg.1/5

Abstract (Equivalent): US 5535090 A

An electrostatic **chuck** for holding an electrically conductive workpiece in a low pressure reactor, the **chuck**, comprising:

a thermally-conductive base plate; a plurality of electrostatic structures disposed over the base plate, each electrostatic structure including:

a first dielectric,  
an electrically conductive electrode forming a first capacitor plate in contact with the first dielectric, and  
a second dielectric in contact with the electrode, and  
a dielectric separator between the first and the second dielectrics and surrounding the electrode, wherein the electrically conductive workpiece forms a second capacitor plate and can be held against the first dielectric of at least one of the electrostatic structures under application of an electrical potential across the first and second capacitor plates.

Dwg.1/5

Title Terms: ELECTROSTATIC; **CHUCK** ; HOLD; CONDUCTING; WORK; PIECE;  
SEMICONDUCTOR; WAFER; ELECTROSTATIC; STRUCTURE; FORMING; ONE; PLATE;  
CAPACITOR; WORKPIECE; FORMING; PLATE

Derwent Class: U11; V06

International Patent Class (Main): H02N-013/00

File Segment: EPI

Manual Codes (EPI/S-X): U11-F02A2; V06-M06F

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